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(54) Title (EN): GAS SENSOR AND METHOD FOR USING SAME

(54) Title (FR): CAPTEUR DE GAZ ET SON PROCÉDÉ DE FABRICATION

(54) Title (JA): ガスセンサ及びその使用方法

(57) Abstract:

(EN): The present invention includes: semiconductor layers (101-103); a graphene film (105) that is provided above the semiconductor layers (101-103), at least a section thereof coming into contact with a gas; and a barrier film (104) between the semiconductor layers (101-103) and the graphene film (105).

(FR): La présente invention comprend : des couches à semi-conducteur (101-103) ; un film de graphène (105) qui est prévu au-dessus des couches à semi-conducteur (101-103), au moins une section de celui-ci venant en contact avec un gaz ; et un film barrière (104) entre les couches à semi-conducteur (101-103) et le film de graphène (105).

(JA): 半導体層(101~103)と、半導体層(101~103)上方に設けられ、少なくとも一部が気体に接するグラフェン膜(105)と、半導体層(101~103)とグラフェン膜(105)との間のバリア膜(104)と、が含まれる。

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